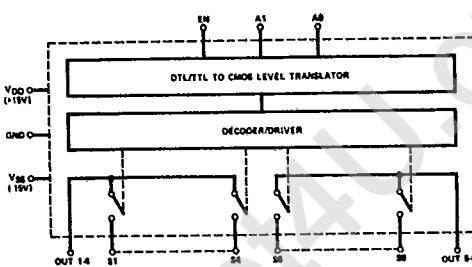


CMOS 4-CHANNEL DIFFERENTIAL ANALOG MULTIPLEXERS

FEATURES

- Latch-Proof
- Overvoltage Protected
- TTL/TTL/CMOS Direct Interface
- Power Dissipation: 30 μ W
- Silicon-Nitride Passivated
- Output "Enable" Control
- Low Power
- Replaces DG509 and HI509A

FUNCTIONAL DIAGRAM



GENERAL DESCRIPTION

The MP7509 is a monolithic, CMOS dual 4-channel analog multiplexer. Depending on the state of two binary address lines and an "enable" input, it switches two output busses to two of 8 inputs.

Very low power dissipation, overvoltage protection and TTL/CMOS direct interfacing are achieved by combining a unique circuit design and a CMOS process. Silicon nitride passivation ensures long term stability while monolithic construction provides reliability.

ABSOLUTE MAXIMUM RATINGS

(T_A = +25°C unless otherwise noted.)

V _{DD} to GND	+17V
V _{SS} to GND	-17V
Overvoltage at V _O (V _S)	
1 second surge	V _{DD} +25V or (V _{SS} -25V)
Continuous	V _{DD} +20V or (V _{SS} -20V)

Switch Current (I_S, Continuous) 35 mA

Switch Current (I_S, Surge)

1mS duration, 10% duty cycle 50 mA

Power Dissipation (Package)*

16 Pin Ceramic DIP**	900 mW
16 Pin Plastic DIP***	470 mW

* Device mounted with all leads soldered or welded to PC board

** Derate 12 mW/°C above +75°C

*** Derate 6.5 mW/°C above +25°C

Operating Temperature

Plastic (K/N)	0°C to +70°C
Ceramic (KD)	-25°C to +85°C
Ceramic (SD)	-55°C to +125°C

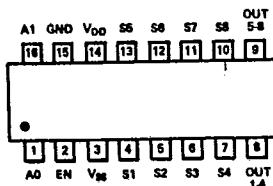
Storage Temperature

-65°C to +150°C

TRUTH TABLE

MP7509				
A ₁	A ₀	E _N	"ON"	
0	0	1	1 & 5	
0	1	1	2 & 6	
1	0	1	3 & 7	
1	1	1	4 & 8	
X	X	0	None	

PIN CONFIGURATION (Top View)



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MICRO POWER SYSTEMS INC

MP7508DI, MP7509DI

T-51-11

SPECIFICATIONS $V_{DD} = +15V$, $V_{SS} = -15V$, unless otherwise noted.

PARAMETER	TEST CONDITION	SWITCH CONDITION	Over Specified			UNITS
			25°C TYP	Temp. Range MIN	MAX	
ANALOG SWITCH						
R_{ON}	$V_s = -10V$ to $+10V$ $I_s = 100\mu A$	ON	400	1000		Ω
ΔR_{ON} Between Switches		ON	4			%
I_s (Input Leakage)	$V_s = -10V$, $V_{out} = +10V$ and $V_s = +10V$, $V_{out} = -10V$	OFF	.1	± 50		nA
I_{out} (OFF Channel Leakage)	"Enable" Low	OFF	1.0	± 250		nA
I_{out} (ON Channel Leakage)	$V_s = -10V$ to $+10V$	ON	.1	± 250		nA
DIGITAL CONTROL						
V_{INL}			0.8	0.8		
V_{INH}			2.4	2.4		V
I_{INL} or I_{INH}			1.0	1.0		μA
DYNAMIC CHARACTERISTICS						
t_A (Access Time); (Note 1)			500	1000		ns
t_{ONEN}	$V_{IN}: 0$ to $5.0V$, $V_{EN}: 0$ to $5.0V$		530	1500		ns
t_{OFFEN}			600	1000		ns
"OFF" Isolation	$V_{EN} = 0.8V$, $R_L = 1K\Omega$ $C_L = 7pf$, $V_s = 3V$ RMS $f = 500K$ Hz		65			dB
C_s (Input Capacitance)		OFF	5			pf
C_{out} (Output Capacitance)	Per Channel	OFF	2.5			pf
C_{os} (Input to Output Capacitance)		OFF	0.1			pf
POWER SUPPLY						
I_{oD}	All Digital Inputs Low	OFF	5	400		μA
I_{ss}	All Digital Inputs Low	OFF	1	400		μA
I_{oD}	All Digital Inputs High	ON	270	2000		μA
I_{ss}	All Digital Inputs High	ON	1	400		μA

NOTES:

- AC parameters are sample tested to insure conformance to specifications.
- KN versions specified for $0^\circ C$ to $+70^\circ C$; KD versions for $-25^\circ C$ to $+85^\circ C$; and SD versions for $-55^\circ C$ to $+125^\circ C$.